

Pages 1 to 16

TRANSISTORS, MATCHED DUAL, NPN

BASED ON TYPE 2N2919, 2N2920 and 2N2920A

ESCC Detail Specification No. 5207/002

Issue 2	October 2008
---------	--------------





LEGAL DISCLAIMER AND COPYRIGHT

European Space Agency, Copyright © 2008. All rights reserved.

The European Space Agency disclaims any liability or responsibility, to any person or entity, with respect to any loss or damage caused, or alleged to be caused, directly or indirectly by the use and application of this ESCC publication.

This publication, without the prior permission of the European Space Agency and provided that it is not used for a commercial purpose, may be:

- copied in whole, in any medium, without alteration or modification.
- copied in part, in any medium, provided that the ESCC document identification, comprising the ESCC symbol, document number and document issue, is removed.



DOCUMENTATION CHANGE NOTICE

(Refer to https://escies.org for ESCC DCR content)

DCR No.	CHANGE DESCRIPTION
187, 334	Specification up issued to incorporate editorial and technical changes per DCR.



ESCC Detail Specification No. 5207/002



ISSUE 2

TABLE OF CONTENTS

<u>1.</u>	<u>GENERAL</u>	<u>5</u>
1.1	Scope	5
1.2	Applicable Documents	5
1.3	Terms, Definitions, Abbreviations, Symbols and Units	5
1.4	The ESCC Component Number and Component Type Variants	5
1.4.1	The ESCC Component Number	5
1.4.2	Component Type Variants	5
1.5	Maximum Ratings	6
1.6	Physical Dimensions and Terminal Identification	7
1.6.1	Metal Can Package (TO-77) - 6 lead	7
1.6.2	Chip Carrier Package (CCP) - 6 terminal	8
1.7	Functional Diagram	9
1.8	Materials and Finishes	9
<u>2.</u>	REQUIREMENTS	9
2.1	General	9
2.1.1	Deviations from the Generic Specification	9
2.2	Marking	10
2.3	Terminal Strength	10
2.4	Electrical Measurements at Room, High and Low Temperatures	10
2.4.1	Room Temperature Electrical Measurements	10
2.4.2	High and Low Temperatures Electrical Measurements	12
2.5	Parameter Drift Values	13
2.6	Intermediate and End-Point Electrical Measurements	14
2.7	Power Burn-in Conditions	15
2.8	Operating Life Conditions	15
ΔΡΡΕΝΙΟΙ	ΙΧ 'Δ'	16



1. **GENERAL**

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 <u>APPLICABLE DOCUMENTS</u>

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. 5000
- (b) MIL-STD-750, Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. 21300 shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 <u>The ESCC Component Number</u>

The ESCC Component Number shall be constituted as follows:

Example: 520700202

Detail Specification Reference: 5207002

Component Type Variant Number: 02 (as required)

1.4.2 <u>Component Type Variants</u>

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g
02	2N2920	TO-77	D2	1
03	2N2920A	TO-77	D2	1
04	2N2919	TO-77	D3 or D4	1
05	2N2920	TO-77	D3 or D4	1
06	2N2920A	TO-77	D3 or D4	1
07	2N2919	TO-77	D7	1
08	2N2920	TO-77	D7	1
09	2N2920A	TO-77	D7	1
10	2N2919	CCP	2	0.2



Variant Number	Based on Type	Case	Lead/Terminal Material and/or Finish	Weight max g
11	2N2920	CCP	2	0.2
12	2N2920A	CCP	2	0.2
13	2N2919	CCP	4	0.2
14	2N2920	CCP	4	0.2
15	2N2920A	CCP	4	0.2

The lead/terminal material and/or finish shall be in accordance with the requirements of ESCC Basic Specification No. 23500.

1.5 **MAXIMUM RATINGS**

The maximum ratings shall not be exceeded at any time during use or storage. Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Unit	Remarks
Collector-Base Voltage	V _{CBO}	60	V	Over entire
Collector-Emitter Voltage	V _{CEO}	60	V	operating temperature
Emitter-Base Voltage	V _{EBO}	6	V	range
Collector Current	I _C	30	mA	Continuous
Power Dissipation (One Section)				At T _{amb} ≤ +25°C Note 1
For TO-77 and CCP	P _{totO1}	0.3	W	
For CCP	P _{totO2}	0.6 (Note 2)	W	
For TO-77	P _{totO3}	0.75	W	At T _{case} ≤ +25°C Note 1
Power Dissipation (Both Sections)				At T _{amb} ≤ +25°C Note 1
For TO-77 and CCP	P _{totB1}	0.5	W	
For CCP	P _{totB2}	1 (Note 2)	W	
For TO-77	P _{totB3}	1.25	W	At T _{case} ≤ +25°C Note 1
Operating Temperature Range	T _{op}	-55 to +200	°C	Note 3
Storage Temperature Range	T _{stg}	-65 to +200	°C	Note 3
Soldering Temperature For TO-77 For CCP	T _{sol}	+260 +245	°C	Note 4 Note 5

NOTES:

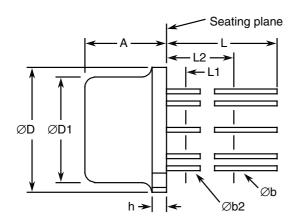
- For T_{amb} or T_{case} > +25°C, derate linearly to 0W at +200°C. When mounted on a 15 x 15 x 0.6mm ceramic substrate.
- For Variants with tin-lead plating or hot solder dip lead finish all testing performed at $T_{amb} > +125^{\circ}C$

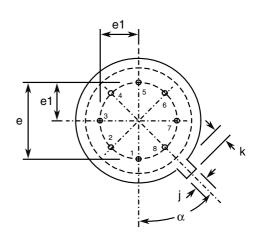


- shall be carried out in a 100% inert atmosphere.
- 4. Duration 10 seconds maximum at a distance of not less than 1.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.
- 5. Duration 5 seconds maximum and the same terminal shall not be resoldered until 3 minutes have elapsed.

1.6 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION

1.6.1 <u>Metal Can Package (TO-77) - 6 lead</u>



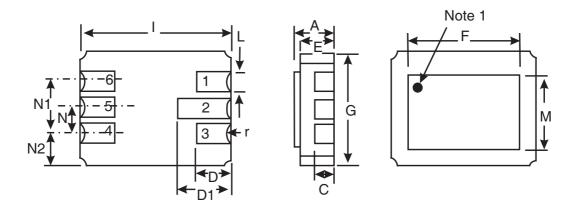


Symbols	Dimensio	Notes	
Symbols	Min	Max	Notes
Α	6.1	6.6	
Øb	0.406	0.533	2, 3
Øb2	0.406	0.483	2, 3
ØD	8.51	9.4	
ØD1	7.75	8.51	
е	5.08	4	
e1	2.54	BSC	4
h	-	1.02	
j	0.711	0.864	
k	0.737	1.14	5
L	12.7	-	2
L1	-	1.27	3
L2	6.35	-	3
α	45° E	BSC	1, 4, 6



- 1. Terminal identification is specified by reference to the tab position where lead 1 = collector 1, lead 2 = base 1, lead 3 = emitter 1, lead 5 = emitter 2, lead 6 = base 2 and lead 7 = collector 2. Lead numbers 4 and 8 are not present on the actual package; they are shown in the drawing for information only.
- 2. Applies to all leads.
- 3. Øb2 applies between L1 and L2. Øb applies between L2 and 12.7mm from the seating plane. Diameter is uncontrolled within L1 and beyond 12.7mm from the seating plane.
- 4. Leads having maximum diameter 0.483mm measured in the gauging plane 1.37(+0.025,-0)mm below the seating plane of the device shall be within 0.178mm of their true position relative to a maximum-width-tab.
- 5. Measured from the maximum diameter of the actual device.
- 6. Tab centreline.

1.6.2 <u>Chip Carrier Package (CCP) - 6 terminal</u>

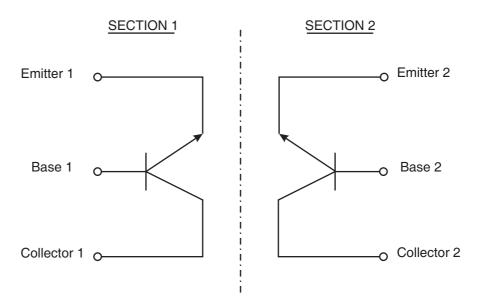


Symbols	Dimension	Notes	
Symbols	Min	Max	Notes
Α	1.53	1.96	
С	0.89 TY	PICAL	2
D	1.52	1.78	
D1	2.08	2.49	
E	1.24	1.55	
F	5.76	5.92	
G	4.19	4.45	
I	6.1	6.35	
L	0.55	0.71	2
M	3.86	4.01	
N	1.14	1.4	
N1	2.41	2.67	
N2	0.89 TY		
r	0.23 TY	PICAL	2



- 1. Terminal identification is specified, when viewing the top side of the package, by reference to a black ink dot adjacent to terminal 1 = base 2. Terminal 2 = collector 2, terminal 3 = emitter 2, terminal 4 = emitter 1, terminal 5 = collector 1 and terminal 6 = base 1.
- 2. Applies to all terminals.

1.7 FUNCTIONAL DIAGRAM



NOTES:

- 1. For TO-77, the case is not connected to any lead.
- 2. For CCP, the lid is not connected to any terminal.

1.8 <u>MATERIALS AND FINISHES</u>

Materials and finishes shall be as follows:

a) Case

For the metal can package the case shall be hermetically sealed and have a metal body with hard glass seals.

For the chip carrier package the case shall be hermetically sealed and have a ceramic body with a Kovar lid.

b) Leads/Terminals

As specified in Component Type Variants.

2. REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this



specification.

2.1.1 <u>Deviations from the Generic Specification</u>

(a) Deviation from Screening Tests - Chart F3
High Temperature Reverse Bias Burn-in and the subsequent Final Measurements for HTRB shall be omitted.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700 and as follows.

The information to be marked on the component shall be:

- (a) Terminal identification (CCP package only).
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number.
- (d) Traceability information.

2.3 <u>TERMINAL STRENGTH</u>

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

For TO-77, Test Condition: E, lead fatigue.

2.4 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

Electrical measurements shall be performed at room, high and low temperatures.

2.4.1 Room Temperature Electrical Measurements

The measurements shall be performed at T_{amb} =+22 ±3°C.

Characteristics	Symbols	-	Test Conditions	Limits		Units
		Test Method		Min	Max	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	3001	I _C = 10μA, Bias condition D	60	-	V
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	3011	I _C = 10mA, Bias condition D, Note 1	60	-	V
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	3026	I _E = 10μA, Bias condition D	6	-	V
Collector-Emitter Cut-off Current	I _{CEO}	3041	V _{CE} = 5V, Bias condition D	-	2	nA



Characteristics	Symbols	MIL-STD-750	Test Conditions	Limits		Units
		Test Method		Min	Max	
Collector-Base Cut-off Current	I _{CBO}	3036	V _{CB} = 45V, Bias condition D	-	2	nA
Collector-Base Cut-off Current	I _{EBO}	3061	V _{EB} = 5V, Bias condition D	-	2	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	3071	I _C =1mA I _B =0.1mA Note 1	-	350	mV
Base-Emitter Saturation Voltage	V _{BE(sat)}	3066	I _C =1mA I _B =0.1mA Test Condition A Note 1	0.5	1	V
Forward-Current Transfer Ratio	h _{FE1}	3076	V _{CE} =5V; I _C = 10μA Variants 04, 07, 10, 13 Variants 02, 03, 05, 06, 08, 09, 11, 12, 14, 15	60 150	240 600	-
	h _{FE2}	3076	V_{CE} =5V ; I_{C} = 100 μ A Variants 04, 07, 10, 13 Variants 02, 03, 05, 06, 08, 09, 11, 12, 14, 15	100 225	-	-
	h _{FE3}	3076	V _{CE} =5V; I _C = 1mA Variants 04, 07, 10, 13 Variants 02, 03, 05, 06, 08, 09, 11, 12, 14, 15	150	-	-
Forward-Current Transfer Ratio Comparison	h _{FE2-1} / h _{FE2-2}	3076	$V_{CE} = 5V ; I_C = 100 \mu A$	0.9	1	-
Base-Emitter Voltage Differential	IV _{BE1} - V _{BE2} l1	3066	$V_{CE} = 5V \; ; \; I_{C} = 10 \mu A$ Test Condition B Variants 02, 04, 05, 07, 08, 10, 11, 13, 14 Variants 03, 06, 09, 12, 15 Note 2	-	5	mV
	IV _{BE1} - V _{BE2} I2	3066	$\begin{array}{c} V_{CE} \! = \! 5V \; ; \; I_{C} = 100 \mu A \\ Test \; Condition \; B \\ Variants \; 02, \; 04, \; 05, \; 07, \\ 08, \; 10, \; 11, \; 13, \; 14 \\ Variants \; 03, \; 06, \; 09, \; 12, \\ 15 \\ Note \; 2 \end{array}$	-	3 1.5	mV
	IV _{BE1} - V _{BE2} I3	3066	V _{CE} =5V ; I _C = 1mA Test Condition B Variants 02, 04, 05, 07, 08, 10, 11, 13, 14 Variants 03, 06, 09, 12, 15 Note 2	-	5 2	mV



Characteristics	Symbols	MIL-STD-750	Test Conditions	Limits		Units
		Test Method		Min	Max	-
Leakage Current Between Sections	I _{LS(e-e)}	-	50V to Emitter 2 0V to Emitter 1	-	5	μΑ
	I _{LS(b-b)}	-	50V to Base 2 0V to Base 1	-	5	μА
	I _{LS(c-c)}	-	50V to Collector 2 0V to Collector 1	-	5	μА
Current Gain Bandwidth Product	f _T	3206	V _{CE} =5V, I _C =500μA f=20MHz Note 3	60	-	MHz
Small-Signal Output Admittance	h _{oe}	3216	V _{CE} =5V, I _C =1mA f=1kHz Note 3	-	1	μmho
Spot Noise Figure	NF _s	3246	V_{CE} =5 V I_{C} =10 μ A R_{s} =10 $k\Omega$ f =1 k Hz BW =200Hz Note 3	-	3	dB
Wide-Band Noise Figure	NF _w	3246	V_{CE} =5 V I_{C} =10 μ A R_{s} =10k Ω 10Hz≤f≤15.7kHz BW=10kHz Note 3	-	3	dB
Output Capacitance	C _{obo}	3236	V _{CB} =5V, I _E =0A 100kHz≤f≤1MHz Note 3	-	6	pF
Small-Signal Input Impedance	h _{ib}	3201	V _{CB} =5V, I _C =1mA f=1kHz Note 3	25	32	Ω

NOTES:

- 1. Pulsed measurement: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 2. Any device whose measurement values exceed the specified limits shall be removed from the lot, but only count for PDA when such values exceed twice the specified limits (e.g., for Base-Emitter Voltage Differential 1: 10mV max or 4mV max).
- 3. For AC characteristics read and record measurements shall be performed on a sample of 32 components with 0 failures allowed. Alternatively a 100% inspection may be performed.



2.4.2 <u>High and Low Temperatures Electrical Measurements</u>

Characteristics	Symbols	MIL-STD-750	Test Conditions	Limits		Units
		Test Method	Note 1	Min	Max	
Collector-Base Cut-off Current	I _{CBO}	3036	T _{amb} =+150(+0-5)°C V _{CB} =45V, Bias Condition D	-	10	μА
Forward-Current Transfer Ratio	h _{FE1}	3076	T _{amb} =-55(+5-0)°C V _{CE} =5V, I _C =10μA Variants 04, 07, 10, 13 Variants 02, 03, 05, 06, 08, 09, 11, 12, 14, 15	20 50	-	-
Forward-Current Transfer Ratio Comparison	h _{FE2-1} / h _{FE2-2}	3076	T_{amb} =-55 to +125°C V_{CE} =5V, I_{C} =100 μ A	0.85	1.18	-
Base-Emitter Voltage Differential Change	IΔ(V _{BE1} - V _{BE2})ΔT _a _{mb} I1	3066	T_{amb} =-55(+5-0)°C to +25±3°C V_{CE} =5V I_{C} =100μA Test condition B Variants 02, 04, 05, 07, 08, 10, 11, 13, 14 Variants 03, 06, 09, 12, 15	-	0.8	mV
	IΔ(V _{BE1} - V _{BE2})ΔT _a _{mb} I2	3066	T_{amb} =+25±3 o C to +125(+0 -5) o C V_{CE} =5 V I_{C} =100 μ A Test condition B Variants 02, 04, 05, 07, 08, 10, 11, 13, 14 Variants 03, 06, 09, 12, 15	-	1 0.5	mV

NOTES:

1. Read and record measurements shall be performed on a sample of 5 components with 0 failures allowed. Alternatively a 100% inspection may be performed.

2.5 <u>PARAMETER DRIFT VALUES</u>

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 ±3°C.

The test methods and test conditions shall be as per the corresponding test defined in Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.



Characteristics	Symbols	Limits			Units	
		Drift			olute	
		Value Δ	Min	Max		
Collector-Base Cut-off Current	І _{СВО}	±0.5 or (1) ±100%	-	2	nA	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	±15 or (1) ±10%	-	350	mV	
Forward-Current Transfer Ratio 2 Variants 04, 07, 10, 13 Variants 02, 03, 05, 06, 08, 09, 11,	h _{FE2}	±15%	100	-		
12, 14, 15			225	-		

1. Whichever is greater, referred to the initial value.

2.6 <u>INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS</u>

Unless otherwise specified, the measurements shall be performed at T_{amb} =+22 $\pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in either Room Temperature Electrical Measurements or High and Low Temperatures Electrical Measurements, as applicable.

The limit values for each characteristic shall not be exceeded.



Characteristics	Symbols	Limits		Units
		Min	Max	
Collector-Base Cut-off Current	I _{CBO}	-	2	nA
Collector-Emitter Saturation Voltage	V _{CE(sat)}	-	350	mV
Forward-Current Transfer Ratio 2 Variants 04, 07, 10, 13 Variants 02, 03, 05, 06, 08, 09, 11, 12,	h _{FE2}	100	-	-
14, 15		225	-	
Forward-Current Transfer Ratio Comparison	h _{FE2-1} / h _{FE2-2}	0.85	1.18	-
Base-Emitter Voltage Differential 2 Variants 02, 04, 05, 07, 08, 10, 11, 13,	IV _{BE1} -V _{BE2} I2			mV
14 Variants 03, 06, 09, 12, 15		-	3 1.5	
Base-Emitter Voltage Differential Change 1 (Note 1) Variants 02, 04, 05, 07, 08, 10, 11, 13,	$ \Delta(V_{BE1}^{-}-V_{BE2})\Delta T_{amb} 1$			mV
14 Variants 03, 06, 09, 12, 15		-	0.96 0.48	
Base-Emitter Voltage Differential Change 2 (Note 1) Variants 02, 04, 05, 07, 08, 10, 11, 13,	$ \Delta(V_{BE1}^{-}) $ $ V_{BE2} \Delta T_{amb} $			mV
14 Variants 03, 06, 09, 12, 15			1.2 0.6	

1. To be measured after Operating Life test only.

2.7 <u>POWER BURN-IN CONDITIONS</u>

Characteristics	Symbols	Test Conditions	Units
Ambient Temperature	T _{amb}	+25 ±3	°C
Power Dissipation (Both Sections)	P _{totB}	As per Maximum Ratings P _{totB1} derated at the chosen T _{amb}	W
Collector-Base Voltage	V _{CB}	40	V

2.8 <u>OPERATING LIFE CONDITIONS</u>

The conditions shall be as specified for Power Burn-in.



APPENDIX 'A'

AGREED DEVIATIONS FOR STMICROELECTRONICS (F)

ITEMS AFFECTED	DESCRIPTION OF DEVIATIONS
TIENS ATTECTED	
Deviations from Production Control- Chart F2	Special In-process Control Internal Visual Inspection. For CCP packages the criteria specified for voids in the fillet and minimum die mounting material around the visible die perimeter for die mounting defects may be omitted providing that a radiographic inspection to verify the die-attach process is performed on a sample basis in accordance with STMicroelectronics procedure 0076637.
Deviations from Room Temperature Electrical Measurements	All AC characteristics (Room Temperature Electrical Measurement Note 2) may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes AC characteristic measurements per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.
Deviations from High and Low Temperatures Electrical Measurements	All characteristics specified may be considered guaranteed but not tested if successful pilot lot testing has been performed on the wafer lot which includes characteristic measurements at high and low temperatures per the Detail Specification. A summary of the pilot lot testing shall be provided if required by the Purchase Order.